3A Current-Limited Power Distribution Switches

General Description

The EMS6040 is an N-channel MOSFET high-side power switch without parasitic body diode between drain and source. The EMS6040 provides very low on-resistance as $58m\Omega$ and continuously delivers up to 3A output current. The fault flag output function indicates fault conditions to the local USB controller. The other features include soft start, current limit protection, Power-On-Reset function, and over temperature protection. The EMS6040 is available in MSOP-8 package.

Ordering Information

Part Number	Package	Remark
EMS6040A	MSOP-8	3A Active Low
EMS6040B	MSOP-8	3A Active High

Features

- Wide Input Range 2.5V to 5.5V
- Low MOSFET On Resistance(58mΩ)
- Low Quiescent(25uA) & Shutdown Current
- Deglitched Open-Drain Fault Flag Output
- Reverse Current Flow Blocking
- Power On Reset Function
- Current Limit Protection
- Over Temperature Protection
- Soft Start and Fast Turn Off
- Reverse Voltage Protection
- Enable Active High or Active Low

Applications

- USB
- Notebook & Netbook &MB

Typical Application

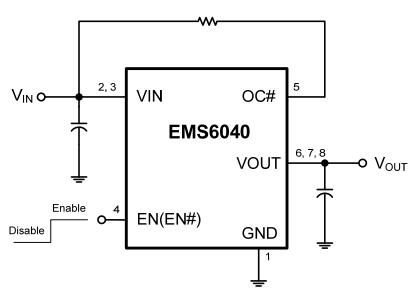
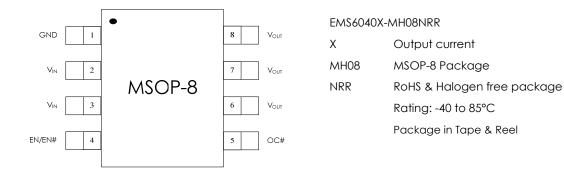


Fig. 1

Note: A low ESR 150uF capacitor between VIN, VOUT & GND is recommended.

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Package Configuration



Order, Mark & Packing information

Package	lout(A)	Product ID	Marking	Packing
		EMS6040A-MH08NRR	ESMT S6040A Tracking code	Tape & Reel
	3.0	EMS6040B-MH08NRR	ESMT S6040B Tracking code 1 2 3 4	3Kpcs

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Functional Block Diagram

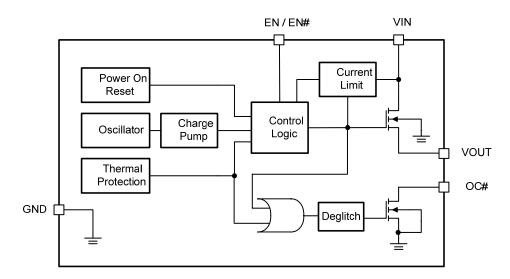


Fig. 2

Pin Functions

Pin Name	SOT-23-5	Function	
GND	1	Ground.	
VIN	2, 3	Input Voltage. This is the drain input to the power device that supplies current to the output pin. Minimum 1uF low ESR ceramic capacitor is recommended at this pin.	
EN/EN#	4	Chip Enable Input (Active high for EN, Active low for EN#)	
OC#	5	OC Flag Output. This is an open-drain output and is set low impedance once curren limit or over temperature protection enabled.	
VOUT	6, 7, 8	Output Voltage. VOUT is power output pin.	

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Absolute Maximum Ratings(Note1)

Devices are subjected to fail if they stay above absolute maximum ratings.

Input Voltage	
Other Pins	
Power Dissipation, PD@TA=25, MSOP-8	0.66W
Package Thermal Resistance, θ _{JA} , MSOP-8 (Note 2)	150°C/W
Junction Temperature	150°C
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature	
ESD susceptibility (Note3)	
HBM (Human Body Mode)	2KV
MM (Machine Mode)	200V

Recommended Operating Conditions(Note4)

Supply Input Voltage, V_{IN} +2.5V to +5.5V
Junction Temperature
Ambient Temperature

Electrical Characteristics

■ VIN=5V, T_A=+25°C, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Supply Input Section						
POR Threshold	V _{PORTH}		-	2.2	2.5	٧
Quiescent Current	lQ	IOUT=0A	-	65	45	υA
Shutdown Current	I _{SD}	EN#=5V	-	0.1	1	υA
Output Voltage		•				
On Resistance	Ron	IOUT=0.5A	-	58	65	mΩ
Reverse Leakage Current	I _{Rev}	VOUT=5V, VIN=0V	-	0.1	2	υA
Soft-Start Time		Rising from 10% to 90%	-	1.5	2	ms
Enable		•				
Enable High Level	V _{EN}		1.2	-	-	٧
Disable Low Level	V _{SD}		-	-	0.5	٧
EN Input Current	I _{EN}		-	0.1	1	υA
OC# Flag Output						•
OC# Output Resistance	R _{FLGB}	ISINK=1mA	-	20	80	Ω
OC# Off Current	I _{FLGB_OFF}	VFLGB=5V	-	0.1	1	υA
OC# Delay Time	T _D		8	15	22	ms
OUT Shutdown Discharge Resistance	R _{DIS}		-	100	-	Ω

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Electrical Characteristics (cont.)

■ VIN=5V, T_A=+25°C, unless otherwise specified.

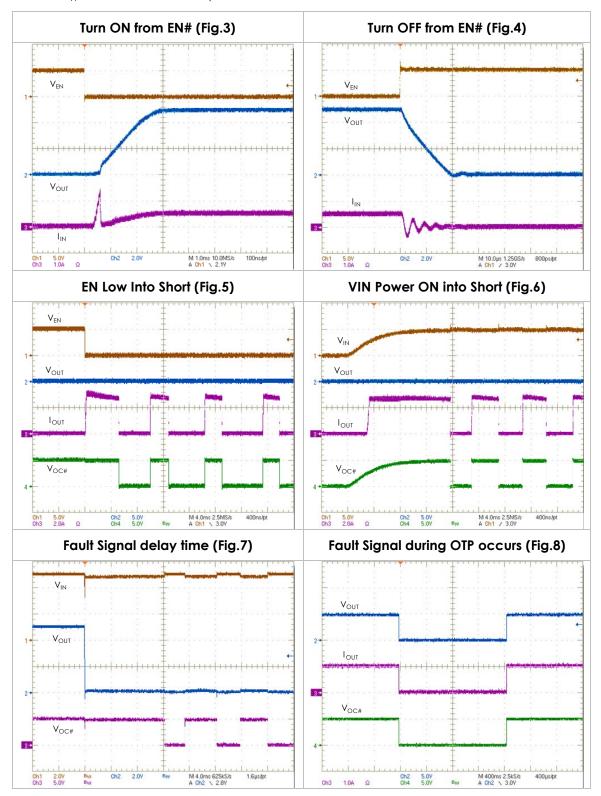
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Protection						
OCP Threshold Level	locp		3.3	3.8	4.3	Α
Output Short Circuit Current	Isc		1.7	2.1	3	Α
Thermal Shutdown Temperature	T _{SD}		-	160	-	$^{\circ}\mathbb{C}$
Thermal Shutdown Hysteresis	T _{SDHYS}		-	30	-	$^{\circ}\mathbb{C}$

- **Note 1.** Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.
- **Note 2.** θ_{JA} is measured in the natural convection at $T_A=25^{\circ}\mathbb{C}$ on a low effective thermal conductivity test board (Single layout, 1S) of JEDEC 51-3 thermal measurement standard.
- **Note 3.** Devices are ESD sensitive. Handling precaution is recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.

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Typical Performance Characteristics

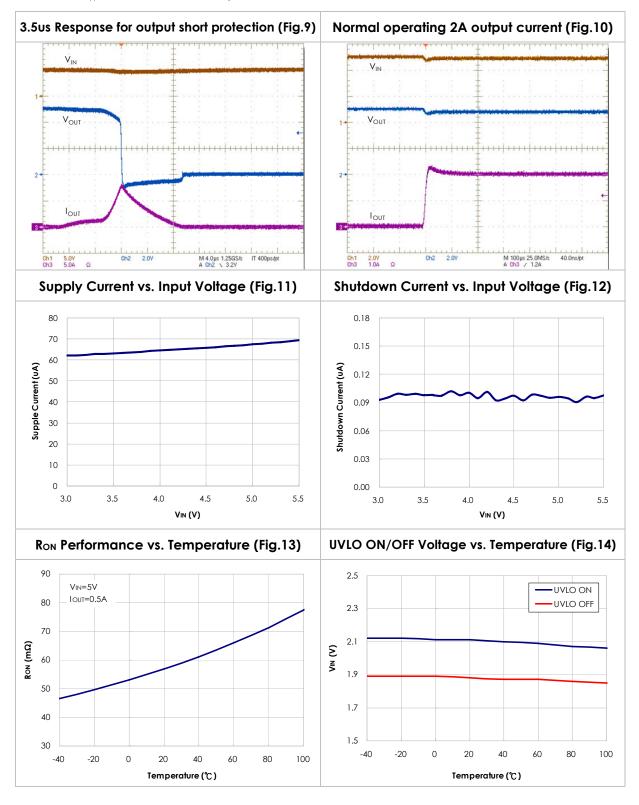
■ V_{IN} =5V, T_A =25 $^{\circ}$ C, unless otherwise specified.



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Typical Performance Characteristics (cont.)

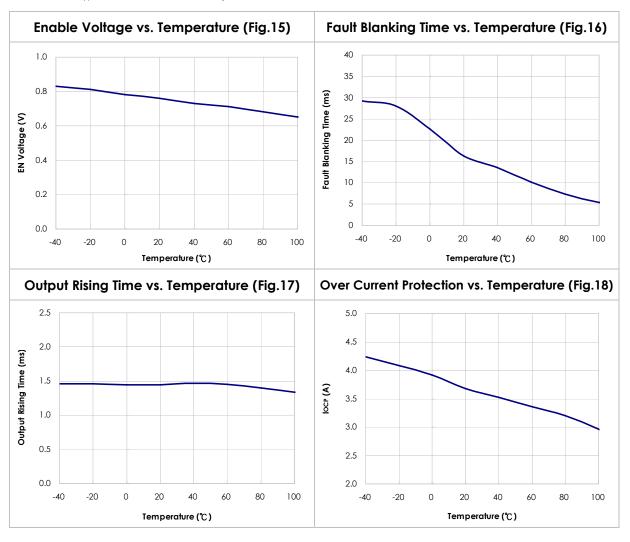
■ V_{IN} =5V, T_A =25°C, unless otherwise specified.



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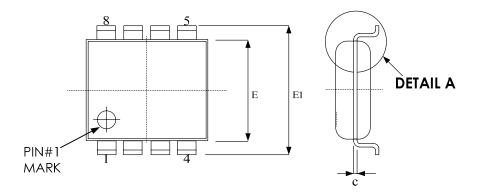
Typical Performance Characteristics (cont.)

■ V_{IN} =5V, T_A =25°C, unless otherwise specified.

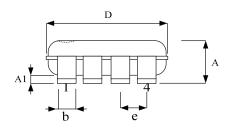


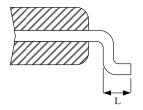
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Package Outline Drawing MSOP-8L (118 mil)



TOP VIEW





SIDE VIEW

DETAIL A

Crusale of	Dimension in mm			
Symbol	Min	Max		
А	0.81	1.10		
A1	0.00	0.15		
Ъ	0.22	0.38		
С	0.13	0.23		
D	2.90	3.10		
Е	2.90	3.10		
E1	4.80	5.00		
е	0.65 BSC			
L	0.40	0.80		

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Revision History

Revision	Date	Description
0.1	2016.04.15	Initial version.
1.0	2016.09.01	Remove preliminary word and modify version to 1.0 Modify order information

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